

AMENDMENT TO THE ABSTRACT:

1. Please amend the Abstract as follows. Applicant attaches to this paper a clean version of the amended Abstract, labeled "Replacement Abstract."

A semiconductor device ~~comprises~~ including a semiconductor substrate, source/drain regions provided in the semiconductor substrate, a gate insulating film provided on a channel region between the source/drain regions, a gate electrode provided on the gate insulating film, a conductive layer of a metal silicide provided on the gate electrode and the source/drain regions, an insulating film ~~containing carbon~~ provided on the semiconductor substrate so as to be in contact with at least the conductive layer, wherein the insulating film contains carbon and is mainly composed of a silicon nitride film, and further contains chlorine at a concentration of $4 \times 10^{21} \text{ cm}^{-3}$ or less, and an interlayer insulating film provided on the semiconductor substrate so as to cover the insulating film ~~containing carbon~~.

REPLACEMENT ABSTRACT

ABSTRACT OF THE DISCLOSURE

A semiconductor device including a semiconductor substrate, source/drain regions provided in the semiconductor substrate, a gate insulating film provided on a channel region between the source/drain regions, a gate electrode provided on the gate insulating film, a conductive layer of a metal silicide provided on the gate electrode and the source/drain regions, an insulating film provided on the semiconductor substrate so as to be in contact with at least the conductive layer, wherein the insulating film contains carbon and is mainly composed of a silicon nitride film, and further contains chlorine at a concentration of $4 \times 10^{21} \text{ cm}^{-3}$ or less, and an interlayer insulating film provided on the semiconductor substrate so as to cover the insulating film.